

**In the Claims:**

1.-20. (Cancelled)

21. (Currently Amended) A method of forming electrically connected contacting parts of a component integrated into a semiconductor substrate, the method comprising:

providing a hard mask over an insulating layer pattern to define a contact hole;

forming said providing a first contact hole in [[an]] said insulating layer;

filling the contact hole with an ARC layer that also overlies said patterned hard mask and the insulating layer;

depositing and patterning a photoresist layer on said ARC layer;

removing portions of the ARC layer and portions of the hard mask not covered by the photoresist layer to repattern said hard mask to define a conductive line trench;

removing portions of the insulating layer to form said conductive line trench;

removing the ARC layer filling from the contact hole; and

filling the contact hole and said conductive line trench with contact material so that the filled contact hole and the conductive line trench are material is electrically connected to a line;

wherein a hard mask that is used to pattern the contact hole is subsequently re-patterned to define a conductor line trench which is connected thereto.

22. (Previously Presented) The method of claim 21 wherein said hard mask is made from polycrystalline silicon.

23. (Previously Presented) The method of claim 21 further comprising patterning said hard mask by means of a dry etching process.

24. (Previously Presented) The method of claim 23 wherein said dry etching process comprises using at least one of the group SF<sub>6</sub>, HBr and He/O<sub>2</sub>.

25. (Currently Amended) The method of claim 21 further comprising depositing a liner on a surface of said contact hole and conductive line trench prior to said step of filling with contact material.

26. (Previously Presented) The method of claim 25 wherein said liner is selected from the group consisting of Ti and TiN.

27. (Currently Amended) The method of claim 21 wherein said step of filling the contact hole with contact material and the conductive line trench comprises comprising filling said contact hole with tungsten.

28. (Cancelled)

29. (Previously Presented) The method of claim 30 wherein said hard mask is made from polycrystalline silicon.

30. (Currently Amended) A method of forming a contact hole and a conductor trench connecting to said contact hole in an insulating layer using a common hard mask, the method comprising:  
providing said insulating layer;  
providing said hard mask over said insulating layer, said hard mask patterned to form said contact hole;

etching said contact hole in said insulating layer subsequent to providing said hard mask ;  
covering said insulating layer with an ARC layer to fill said contact hole;  
depositing and patterning a photoresistive layer that covers said ARC layer;  
re-patterning said hard mask subsequent to said step of covering [[the]] said insulating layer with [[an]] said ARC layer to form to define said conductor trench connected to said contact hole;

etching said conductor trench in said insulating layer according to said re-patterned hard mask ; and

filling said contact hole and said conductor trench with a conductive material such that said conductive material in said conductor trench and said contact hole are electrically connected.

31. (Currently Amended) The method of claim 30 wherein said step of repatterning re-patterning said hard mask comprises etching said hard mask by means of a dry etching process.

32. (Previously Presented) The method of claim 31 wherein said dry etching process comprises using at least one of the group SF<sub>6</sub>, HBr and He/O<sub>2</sub>.

33. (Currently Amended) The method of claim 30 further comprising [[the]] a step of depositing a liner on a surface of said contact hole and conductor trench prior to said step of filling.

34. (Currently Amended) The method of claim 30 wherein said step of filling said contact hole and conductor trench with conductive material comprises filling said contact hole and conductor trench with tungsten.

35. (Previously Presented) The method of claim 33 wherein said liner is selected from the group consisting of Ti and TiN.